

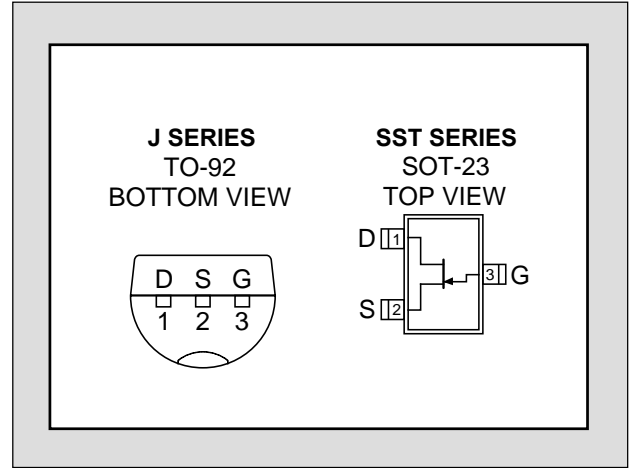
LINEAR SYSTEMS

Linear Integrated Systems

FEATURES	
DIRECT REPLACEMENT FOR SILICONIX J/SST201 SERIES	
LOW CUTOFF VOLTAGE	$V_{GS(off)} \leq 1.5V$
HIGH GAIN	$A_v = 80 V/V$
ABSOLUTE MAXIMUM RATINGS ¹	
@ 25 °C (unless otherwise stated)	
Maximum Temperatures	
Storage Temperature	-65 to +150 °C
Operating Junction Temperature	-55 to +135 °C
Maximum Power Dissipation	
Continuous Power Dissipation	350mW
Maximum Current	
Forward Gate Current	50mA
Maximum Voltages	
Gate to Drain Voltage	-40V
Gate to Source Voltage	-40V

J/SST201 SERIES

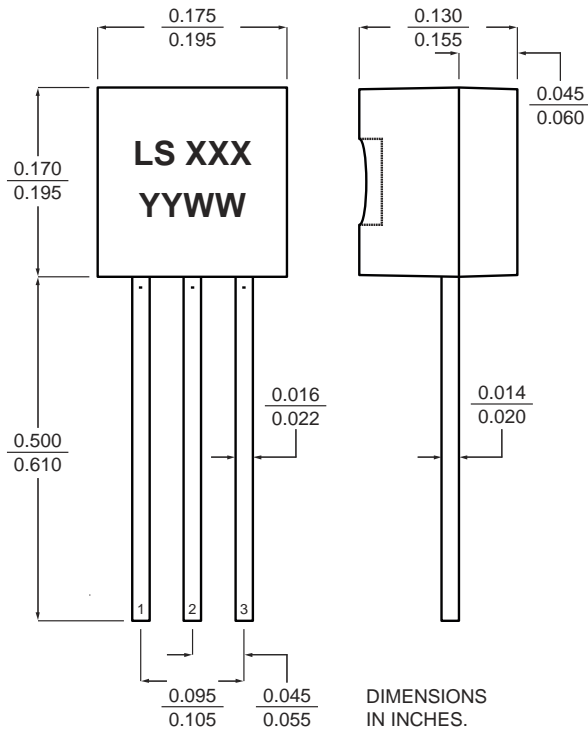
**HIGH GAIN
N-CHANNEL JFET**



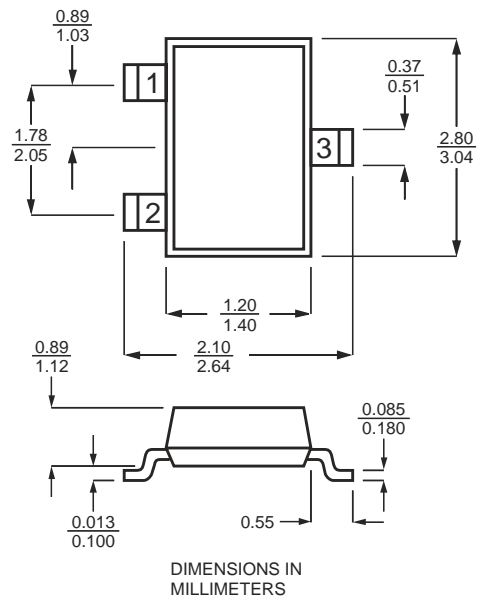
ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS	
BV _{GSS}	Gate to Source Breakdown Voltage	J/SST201, 202	-40			V	I _G = -1μA, V _{DS} = 0V
		J/SST204	-25				
V _{GS(off)}	Gate to Source Cutoff Voltage	J/SST201	-0.3		-1.5	V	V _{DS} = 15V, I _D = 10nA
		J/SST202	-0.8		-4		
		J/SST204	-0.3		2		
I _{DSS}	Drain to Source Saturation Current ²	J/SST201	0.2		1	mA	V _{DS} = 15V, V _{GS} = 0V
		J/SST202	0.9		4.5		
		J/SST204	0.2		3		
I _{GSS}	Gate Reverse Current	-2		-100	pA	V _{GS} = -20V, V _{DS} = 0V	
I _G	Gate Operating Current		-2			V _{DG} = 10V, I _D = 0.1mA	
I _{D(off)}	Drain Cutoff Current		2			V _{DS} = 15V, V _{GS} = -5V	
g _{fs}	Forward Transconductance	J/SST201, 204	0.5			mS	V _{DS} = 15V, V _{GS} = 0V, f = 1kHz
		J/SST202	1				
C _{iss}	Input Capacitance		4.5		pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	
C _{rss}	Reverse Transfer Capacitance		1.3				
e _n	Noise Voltage		6		nV/√Hz	V _{DS} = 10V, V _{GS} = 0V, f = 1kHz	

TO-92



SOT-23



1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. Pulse Test: $PW \leq 300\mu s$, Duty Cycle $\leq 3\%$

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